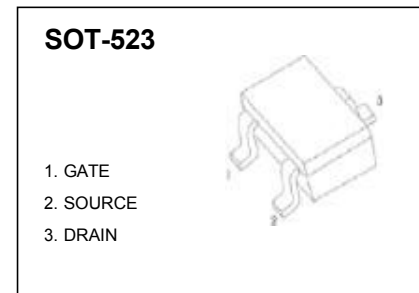


$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
50 V	3Ω@10V	200mA
	4Ω@5V	



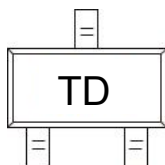
FEATURE

- High density cell design for low $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

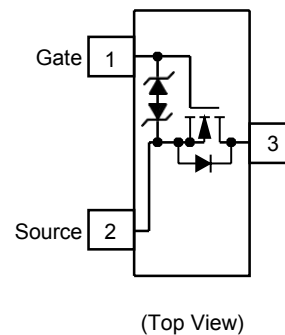
APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



Equivalent Circuit



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source voltage	50	V
V_{GS}	Gate-Source voltage	20	V
I_D	Drain Current	200	mA
P_D	Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	833	$^\circ\text{C/W}$
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

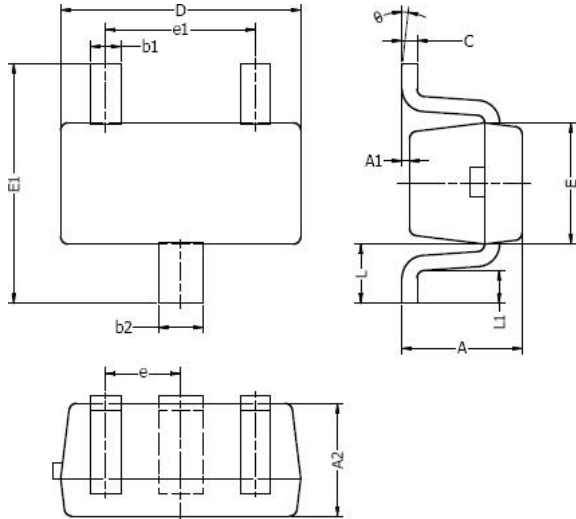
**MOSFET ELECTRICAL CHARACTERISTICS****T_a=25 °C unless otherwise specified**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	50			V
Gate-Threshold Voltage	$V_{th(GS)}$	$V_{DS}=V_{GS}, I_D=250\text{ }\mu\text{A}$	0.7	1.0	1.5	
Gate-body Leakage	I_{GSS}	$V_{DS}=0\text{ V}, V_{GS}=\pm 20\text{ V}$			± 10	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60\text{ V}, V_{GS}=0\text{ V}$			± 30	μA
On-state Drain Current	$I_{D(ON)}$	$V_{GS}=10\text{ V}, V_{DS}=7\text{ V}$	200			mA
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=500\text{mA}$		2	3	Ω
		$V_{GS}=5\text{ V}, I_D=50\text{mA}$		3	4	
Forward Trans conductance	g_{fs}	$V_{DS}=10\text{ V}, I_D=200\text{mA}$	80			ms
Drain-source on-voltage	$V_{DS(on)}$	$V_{GS}=10\text{V}, I_D=500\text{mA}$			3.75	V
		$V_{GS}=5\text{V}, I_D=50\text{mA}$			0.375	V
Diode Forward Voltage	V_{SD}	$I_S=115\text{mA}, V_{GS}=0\text{ V}$	0.55		1.2	V
Input Capacitance	C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$			50	pF
Output Capacitance	C_{oss}				25	
Reverse Transfer Capacitance	C_{rss}				5	

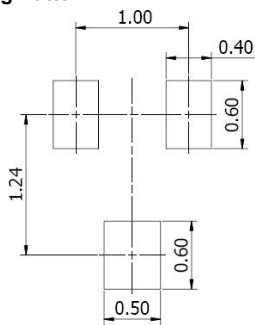
SWITCHING TIME

Turn-on Time	$t_{d(on)}$	$V_{DD}=25\text{ V}, R_L=50\text{ }\Omega$			20	ns
Turn-off Time	$t_{d(off)}$	$I_D=500\text{mA}, V_{GEN}=10\text{ V}$ $R_G=25\text{ }\Omega$			40	

SOT-523 Package Outline



Typical Soldering Pattern:



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
A1	0.00	0.10	0.000	0.004
A2	0.70	0.80	0.028	0.031
b1	0.15	0.25	0.006	0.010
b2	0.25	0.35	0.010	0.014
c	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
E1	1.45	1.75	0.057	0.069
e	0.50 TYP.		0.020 TYP.	
e1	0.90	1.10	0.035	0.043
L	0.40 REF.		0.016 REF.	
L1	0.10	0.30	0.004	0.012
θ	0°	8°	0°	8°

NOTES:

1. Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.